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Substitute for form 1449A/B/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (Use as many sheets as necessary)				<b>Complete if Known</b>	
				Application Number	10/663,741
				Filing Date	September 17, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	2811
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	M4065.0656/P656
Sheet	1	of	1		

## U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Document Number Number-Kind Code <sup>2</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
Ch	A	6,673,648	01/06/2004	Lowrey	

## FOREIGN PATENT DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document Country Code <sup>3</sup> -Number <sup>4</sup> -Kind Code <sup>5</sup> (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>

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## NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>

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*Reply*

02-15-05



Approved for use through 07/31/2008. OMB 0651-0031  
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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code <sup>2</sup> (if known)			
CA	A	US 2004/0035401	2/2004	Ramachandran et al.	
CA	B	US 2003/0212724	11/2003	Ovshinsky et al.	
CA	C	US 2003/0048744	3/2003	Ovshinsky et al.	
CA	D	US 2003/0212725	11/2003	Ovshinsky et al.	
CA	E	US RE 37,259E	7/2001	Ovshinsky	
CA	F	US 3,271,591	9/1966	Ovshinsky	
CA	G	US 3,961,314	6/1976	Klose et al.	
CA	H	US 3,966,317	6/1976	Wacks et al.	
CA	I	US 3,983,542	11/1976	Ovshinsky	
CA	J	US 3,988,720	10/1976	Ovshinsky	
CA	K	US 4,177,474	12/1979	Ovshinsky	
CA	L	US 4,267,261	5/1981	Hallman et al.	
CA	M	US 4,597,162	7/1986	Johnson et al.	
CA	N	US 4,608,296	8/1986	Keem et al.	
CA	O	US 4,637,895	1/1987	Ovshinsky et al.	
CA	P	US 4,646,266	2/1987	Ovshinsky et al.	
CA	Q	US 4,664,939	5/1987	Ovshinsky	
CA	R	US 4,668,968	5/1987	Ovshinsky et al.	
CA	S	US 4,670,763	6/1987	Ovshinsky et al.	
CA	T	US 4,673,957	6/1987	Ovshinsky et al.	
CA	U	US 4,678,679	7/1987	Ovshinsky	
CA	V	US 4,696,758	9/1987	Ovshinsky et al.	
CA	W	US 4,698,234	10/1987	Ovshinsky et al.	
CA	X	US 4,710,899	12/1987	Young et al.	
CA	Y	US 4,728,406	3/1988	Banerjee et al.	
CA	Z	US 4,737,379	4/1988	Hudgens et al.	
CA	A1	US 4,766,471	8/1988	Ovshinsky et al.	
CA	B1	US 4,769,338	9/1988	Ovshinsky et al.	
CA	C1	US 4,775,425	10/1988	Guha et al.	
CA	D1	US 4,788,594	11/1988	Ovshinsky et al.	
CA	E1	US 4,809,044	2/1989	Pryor et al.	
CA	F1	US 4,818,717	4/1989	Johnson et al.	
CA	G1	US 4,843,443	6/1989	Ovshinsky et al.	
CA	H1	US 4,845,533	7/1989	Pryor et al.	
CA	I1	US 4,853,785	8/1989	Ovshinsky et al.	
CA	J1	US 4,891,330	1/1990	Guha et al.	
CA	K1	US 5,128,099	7/1992	Strand et al.	
CA	L1	US 5,159,661	10/1992	Ovshinsky et al.	
CA	M1	US 5,166,758	11/1992	Ovshinsky et al.	
CA	N1	US 5,177,567	1/1993	Klersy et al.	
CA	O1	US 5,296,716	3/1994	Ovshinsky et al.	
CA	P1	US 5,335,219	8/1994	Ovshinsky et al.	
CA	Q1	US 5,359,205	10/1994	Ovshinsky	
CA	R1	US 5,341,328	8/1994	Ovshinsky et al.	
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Sheet	2	of	3	Attorney Docket Number	M4065.0656/P656

On	T1	US 5,414,271	5/1995	Ovshinsky et al.	
On	U1	US 5,534,711	7/1996	Ovshinsky et al.	
On	V1	US 5,534,712	7/1996	Ovshinsky et al.	
On	W1	US 5,536,947	7/1996	Klersy et al.	
On	X1	US 5,543,737	8/1996	Ovshinsky	
On	Y1	US 5,591,501	1/1997	Ovshinsky et al.	
On	Z1	US 5,596,522	1/1997	Ovshinsky et al.	
On	A2	US 5,687,112	11/1997	Ovshinsky	
On	B2	US 5,694,054	12/1997	Ovshinsky et al.	
On	C2	US 5,714,768	2/1998	Ovshinsky et al.	
On	D2	US 5,825,046	10/1998	Czubatyj et al.	
On	E2	US 5,912,839	6/1999	Ovshinsky et al.	
On	F2	US 5,933,365	8/1999	Klersy et al.	
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On	H2	US 6,087,674	7/2000	Ovshinsky et al.	
On	I2	US 6,141,241	10/2000	Ovshinsky et al.	
On	J2	US 6,339,544	1/2002	Chiang et al.	
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On	M2	US 6,437,383	8/2002	Xu	
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On	R2	US 6,507,061	1/2003	Hudgens et al.	
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On	T2	US 6,511,867	1/2003	Lowery et al.	
On	U2	US 6,512,241	1/2003	Lai	
On	V2	US 6,514,805	2/2003	Xu et al.	
On	W2	US 6,531,373	3/2003	Gill et al.	
On	X2	US 6,534,781	3/2003	Dennison	
On	Y2	US 6,545,287	4/2003	Chiang	
On	Z2	US 6,545,907	4/2003	Lowery et al.	
On	A3	US 6,555,860	4/2003	Lowery et al.	
On	B3	US 6,563,164	5/2003	Lowery et al.	
On	C3	US 6,566,700	5/2003	Xu	
On	D3	US 6,567,293	5/2003	Lowery et al.	
On	E3	US 6,569,705	5/2003	Chiang et al.	
On	F3	US 6,570,784	5/2003	Lowery	
On	G3	US 6,576,921	6/2003	Lowery	
On	H3	US 6,586,761	7/2003	Lowery	
On	I3	US 6,589,714	7/2003	Maimon et al.	
On	J3	US 6,590,807	7/2003	Lowery	
On	K3	US 6,593,176	7/2003	Dennison	
On	L3	US 6,597,009	7/2003	Wicker	
On	M3	US 6,605,527	8/2003	Dennison et al.	
On	N3	US 6,613,604	9/2003	Maimon et al.	
On	O3	US 6,621,095	9/2003	Chiang et al.	
On	P3	US 6,625,054	9/2003	Lowery et al.	
On	Q3	US 6,642,102	11/2003	Xu	

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			Art Unit	2811	
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Sheet	3	of	3	Attorney Docket Number	M4065.0656/P656

<i>an</i>	R3	US 6,646,297	11/2003	Dennison	
<i>an</i>	S3	US 6,649,928	11/2003	Dennison	
<i>an</i>	T3	US 6,667,900	12/2003	Lowery et al.	
<i>an</i>	U3	US 6,671,710	12/2003	Ovshinsky et al.	
<i>an</i>	V3	US 6,673,700	1/2004	Dennison et al.	
<i>an</i>	W3	US 6,674,115	1/2004	Hudgens et al.	
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<i>an</i>	Y3	US 6,690,026	2/2004	Peterson	
<i>an</i>	Z3	US 6,696,355	2/2004	Dennison	
<i>an</i>	A4	US 6,687,153	2/2004	Lowery	
<i>an</i>	B4	US 6,707,712	3/2004	Lowery	
<i>an</i>	C4	US 6,714,954	3/2004	Ovshinsky et al.	

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PTO/SB/08a/b (08-03)  
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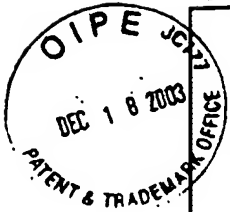
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CA	CA	YOJI KAWAMOTO et al., "Ionic Conduction in As <sub>2</sub> S <sub>3</sub> -Ag <sub>2</sub> S, GeS <sub>2</sub> -GeS <sub>2</sub> -GeS-Ag <sub>2</sub> S and P <sub>2</sub> S <sub>5</sub> -Ag <sub>2</sub> S Glasses," Journal of Non-Crystalline Solids 20 (1976) 393-404.	

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Art Unit	N/A
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Attorney Docket Number	M4065.0656/P656

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		Number-Kind Code <sup>2</sup> (if known)			
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CA	AB	2002/0072188	6/13/2002	Gilton	
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CA	AH	2002/0123169	09/05/2002	Moore et al.	
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CA	AJ	2002/0123248	09/05/2002	Moore et al.	
CA	AK	2002/0127886	09/12/2002	Moore et al.	
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CA	AF	2002/0160551	10/31/2002	Harshfield	
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CA	AR	2003/0027416	02/06/2003	Moore	
CA	AS	2003/0032254	02/13/2003	Gilton	
CA	AT	2003/0035314	02/20/2003	Kozicki	
CA	AU	2003/0035315	02/20/2003	Kozicki	
CA	AV	2003/0038301	02/27/2003	Moore	
CA	AW	2003/0043631	03/06/2003	Gilton et al.	
CA	AX	2003/0045049	03/06/2003	Campbell et al.	
CA	AY	2003/0045054	03/06/2003	Campbell et al.	
CA	AZ	2003/0047765	03/13/2003	Campbell	
CA	AA1	2003/0047772	03/13/2003	Li	
CA	AB1	2003/0047773	03/13/2003	Li	
CA	AC1	2003/0048519	03/13/2003	Kozicki	
CA	AD1	2003/0049912	03/13/2003	Campbell et al.	
CA	AE1	2003/0068861	04/10/2003	Li	
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CA	AG1	2003/0095426	05/22/2003	Hush et al.	
CA	AH1	2003/0096497	05/22/2003	Moore et al.	
CA	AI1	2003/0107105	06/12/2003	Kozicki	
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CA	AQ1	2003/0156463	08/21/2003	Casper et al.	
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CA	AS1	3,743,847	7/1973	Boland	
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<input checked="" type="checkbox"/>	AW2	5,846,889	12/1998	Harbison et al.	
<input checked="" type="checkbox"/>	AX2	5,851,882	12/22/1998	Harshfield	
<input checked="" type="checkbox"/>	AY2	5,869,843	2/9/1999	Harshfield	
<input checked="" type="checkbox"/>	AZ2	5,896,312	4/20/1999	Kozicki et al.	
<input checked="" type="checkbox"/>	AA3	5,914,893	6/22/1999	Kozicki et al.	
<input checked="" type="checkbox"/>	AB3	5,920,788	7/1999	Reinberg	
<input checked="" type="checkbox"/>	AC3	5,998,066	12/1999	Block et al.	
<input checked="" type="checkbox"/>	AD3	6,031,287	2/29/2000	Harshfield	
<input checked="" type="checkbox"/>	AE3	6,072,716	06/06/2000	Jacobson et al.	
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<input checked="" type="checkbox"/>	AG3	6,084,796	7/4/2000	Kozicki et al.	
<input checked="" type="checkbox"/>	AH3	6,177,338	1/2001	Liaw et al.	
<input checked="" type="checkbox"/>	AI3	6,117,720	9/2000	Harshfield	
<input checked="" type="checkbox"/>	AJ3	6,143,604	11/2000	Chiang et al.	
<input checked="" type="checkbox"/>	AK3	6,236,059	5/2001	Wolsteinholme et al.	
<input checked="" type="checkbox"/>	AL3	6,297,170	10/2001	Gabriel et al.	
<input checked="" type="checkbox"/>	AM3	6,300,684	10/2001	Gonzalez et al.	
<input checked="" type="checkbox"/>	AN3	6,316,784	11/2001	Zahorik et al.	
<input checked="" type="checkbox"/>	AO3	6,329,606	12/2001	Freyman et al.	
<input checked="" type="checkbox"/>	AP3	6,348,365	2/19/2002	Moore et al.	
<input checked="" type="checkbox"/>	AQ3	6,350,679	2/2002	McDaniel et al.	

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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Application Number	10/663,741
		Filing Date	September 17, 2003
		First Named Inventor	Terry L. Gilton
		Art Unit	N/A
		Examiner Name	Not Yet Assigned
Sheet 3 of 11	Attorney Docket Number	M4065.0656/P656	

<input checked="" type="checkbox"/>	AR3	6,376,284	4/2002	Gonzalez et al.	
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<input checked="" type="checkbox"/>	AV3	6,418,049	7/9/2002	Kozicki et al.	
<input checked="" type="checkbox"/>	AW3	6,420,725	7/16/2002	Harshfield	
<input checked="" type="checkbox"/>	AX3	6,423,628	7/2002	Li et al.	
<input checked="" type="checkbox"/>	AY3	6,440,837	8/27/2002	Harshfield	
<input checked="" type="checkbox"/>	AZ3	6,469,364	10/2002	Kozicki	
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<input checked="" type="checkbox"/>	AI4	2002/0159292	10/31/2002	Forbes	
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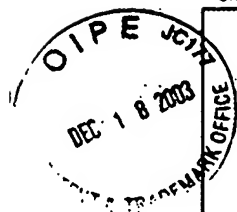
FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. <sup>1</sup>	Foreign Patent Document		Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T
		Country Code <sup>2</sup> -Number <sup>3</sup> -Kind Code <sup>4</sup> (if known)					
<i>g</i>	BA	56126916		10/19981	Akira et al.		
<i>h</i>	BB	WO 97/48032		12/18/1997	Kozicki et al.		
<i>h</i>	BC	WO 99/28914		06/10/1999	Kozicki et al.		
<i>g</i>	BD	WO 00/48196		08/17/2000	Kozicki et al.		
<i>h</i>	BE	WO 02/21542		03/14/2002	Kozicki et al.		

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		First Named Inventor	Terry L. Gilton		
		Group Art Unit	N/A		
		Examiner Name	Not Yet Assigned		
Sheet	4	of	11	Attorney Docket Number	M4065.0656/P656

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.		T <sup>2</sup>
an	CA	Abdel-All, A.; Elshafie, A.; Elhawary, M.M., DC electric-field effect in bulk and thin-film Ge <sub>5</sub> As <sub>38</sub> Te <sub>57</sub> chalcogenide glass, Vacuum 59 (2000) 845-853.		
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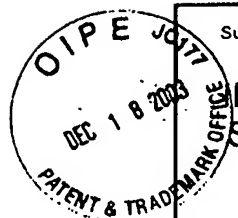
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## Complete if Known

Application Number	10/663,741
Filing Date	September 17, 2003
First Named Inventor	Terry L. Gilton
Group Art Unit	N/A
Examiner Name	Not Yet Assigned

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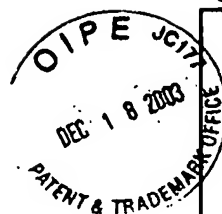
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Examiner Name	Not Yet Assigned
Attorney Docket Number	M4065.0656/P656

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Sheet	7	of	11	Attorney Docket Number	M4065.0656/P656

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